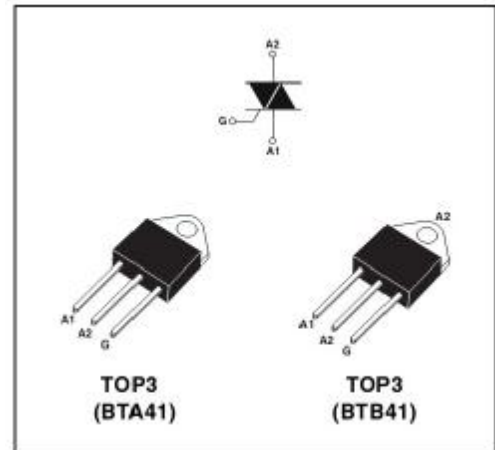


**Features:**

- NPNPN Bi-direction Triac
- Back multilayer metal electrode
- High temperature reliability
- Glass Passivated junction chipses

**Application:**

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**•Limiting Values**

Symbol	Absolute maximum ratings Parameters			Value	Unit
IT(RMS)	RMS on-state current	BTA BTB	Tc=80°C Tc=90°C	40	A
ITSM	Non repetitive surge peak on-state current	F=50HZ	t=20ms	410	A
i <sup>2</sup> t	I <sup>2</sup> t value for fusing	tp=10ms		880	A <sup>2</sup> S
di/dt	Critical rate of rise of on-state current		Tj=125°C	50	A/us
VDRM/VRRM	Non repetitive surge peak off-state voltage		Tj=25°C	600	V
IGM	Peak gate current	tp=20us	Tj=125°C	8	A
PG(AV)	Average gate power dissipation		Tj=125°C	1	W
Tstg	Storage junction temperature range			-40to+150	°C
Tj	Operating junction temperature range			-40to+125	

• **Electrical Characteristics(4 quadrant) (T<sub>j</sub>=25°C, unless otherwise specified)**

Symbol	Test Condition	Quadrant		Value	Unit
I <sub>GT</sub>	V <sub>D</sub> =12V R <sub>L</sub> =100Ω	I II III IV	MAX	I II IV	mA
V <sub>GT</sub>				50	
V <sub>GD</sub>	T <sub>j</sub> =125°C		MIN	1.5	V
I <sub>H</sub>	I <sub>T</sub> =0.5A		MAX	0.2	V
I <sub>L</sub>	I <sub>G</sub> =1.2I <sub>GT</sub>	I II IV	MAX	80	mA
		IV		70	
dv/dt	V <sub>D</sub> =2/3V <sub>DRM</sub> T <sub>j</sub> =125°C		MIN	800	V/us
(dv/dt) <sub>c</sub>	T <sub>j</sub> =125°C		MIN	10	V/us

• **Static Characteristics**

Symbol	Test Conditions			Value	Unit	
V <sub>TM</sub>	I <sub>TM</sub> = 82A	T <sub>j</sub> =25°C	MAX	1.55	V	
V <sub>T0</sub>	Threshold voltage		T <sub>j</sub> =125°C	MAX	0.86	V
R <sub>d</sub>	Dynamic resistance		T <sub>j</sub> =125°C	MAX	6.4	mΩ
I <sub>DRM</sub> I <sub>RRM</sub>	V <sub>DRM</sub> = V <sub>DRM</sub>		T <sub>j</sub> =25°C T <sub>j</sub> =125°C	MAX	10	uA
					2	mA
R <sub>th(j-c)</sub>	Junction to case (AC)		BTA	0.9	°C/W	
			BTB	0.6		

● TO-3P Dimension

